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(71) Applicant: HEWLETT-PACKARD COMPANY [US/US]; Legal Department, M/S 20BN, 3000 Hanover Street, Palo Alto, CA 94304-1112 (US).

(72) Inventor: KAMINS, Theodore; 4132 Thain Way, Palo Alto, CA 94306 (US).

(74) Agent: SCHUYLER, Marc P.; Hewlett-Packard Company, Intellectual Property, P.O. Box 272400, M/S 35, Fort Collins, CO 80527-2400 (US).

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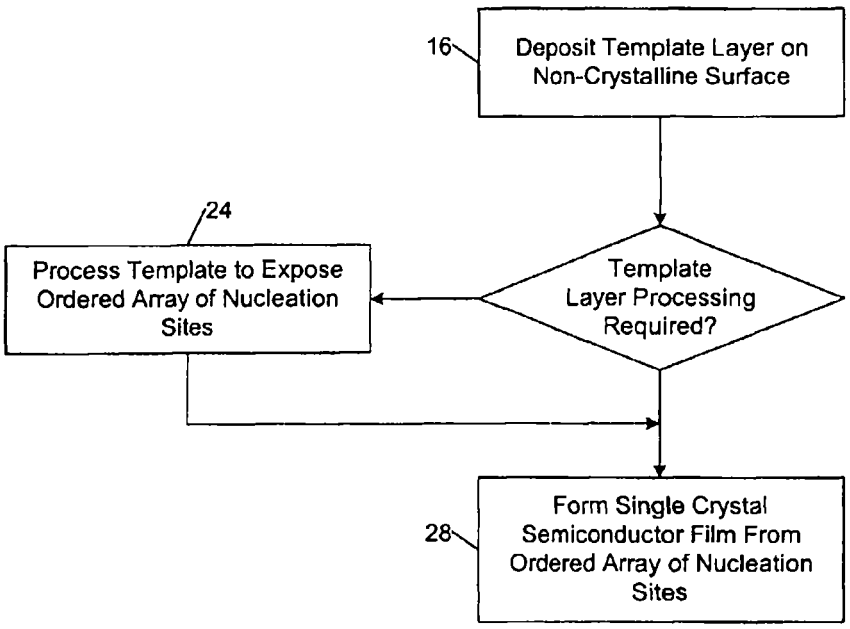
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(54) Title: FORMING A SINGLE CRYSTAL SEMICONDUCTOR FILM ON A NON-CRYSTALLINE SURFACE



(57) Abstract: A method of forming a single crystal semiconductor film on a non-crystalline surface is described. In accordance with this method, a template layer incorporating an ordered array of nucleation sites is deposited on the non-crystalline surface, and the single crystal semiconductor film is formed on the non-crystalline surface from the ordered array of nucleation sites. An integrated circuit incorporating one or more single crystal semiconductor layers formed by this method also is described.

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